



Docket No.
87552.99R134/SE-906D

Ab
Qm
W/16/08

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

Applicant	:	Linn et al.) Examiner:
Serial No.	:	09/316,580) S. Loke
Filed	:	May 21, 1999) Art Unit:
For	:	BONDED WAFER WITH METAL SILICIDATION) 2811

AMENDMENT UNDER 37 CFR §1.116
AND REQUEST FOR RECONSIDERATION

Assistant Commissioner for Patents
Washington, D.C. 20231
Box AF

Dear Sir:

In response to the Office Action mailed January 6, 2000, please amend the above-identified application as follows:

In the Claims:

Amend claim 4 as follows:

not OK
4. (Amended) The integrated circuit of claim [1] 7 wherein said device silicon layer includes deep buried layers abutting said second dielectric layer.

Amend claim 5 as follows:

not OK
5. (Amended) The integrated circuit of claim [1] 7 wherein said handle [wafer] die comprises silicon and [at least one of said dielectric dielectric layers] said first dielectric layer comprises diamond.

Further amend claim 10 as follows:

not OK
10. (Twice amended) A bonded wafer integrated circuit comprising:
(a) a handle die comprising a first dielectric layer, said first dielectric layer comprising a first bonding material;